

1 Mbit/s High Speed Transistor Coupler

Features

- High speed 1Mbit/s
- High isolation voltage between input and output (Viso=3750 Vrms)
- Guaranteed CTR performance from 0°C to 70°C
- Wide operating temperature range of -55°C to 100°C
- Green Package
- Regulatory Approvals
 - UL UL1577 (E364000)
 - VDE EN60747-5-5(VDE0884-5)
 - CQC GB4943.1, GB8898
 - IEC60065, IEC60950

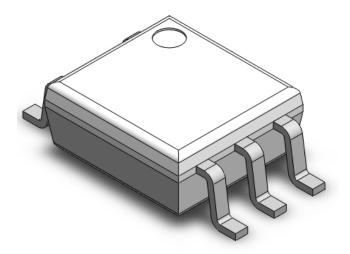
Description

The CTM452 and CTM453 devices each consist of an infrared emitting diode, optically coupled to a high speed photo detector transistor. A separate connection for the photodiode bias output-transistor collector increase the speed by several orders of magnitude over conventional couplers phototransistor by reducing the base-collector capacitance of the input transistor. The devices are packaged in a Mini-Flat package.

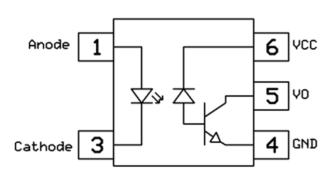
Applications

- Line receivers
- Telecommunication equipment
- Feedback loop in switch-mode power supplies
- Home appliances
- High speed logic ground isolation

Package Outline



Schematic





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Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage *1	3750	V _{RMS}	
Topr	Operating temperature	-55 ~ +100	°C	
Тѕтс	Storage temperature	-55 ~ +125	°C	
TsoL	Soldering temperature *2	260	°C	
Emitter		·		
l _F	Forward current	25	mA	
I _{FP}	Peak forward current (50% duty, 1ms P.W)	50	mA	
I _{F(TRANS)}	Peak transient current (≤1µs P.W,300pps)	1	А	
V _R	Reverse voltage	5	V	
P _D	Power dissipation	45	mW	
Detector				
PD	Power dissipation	100	mW	
I _{O(AVG)}	Average Output current	8	mA	
I _{O (Peak)}	Peak Output current	16	mA	
Vo	Output voltage	-0.5 to 20	V	
Vcc	Supply voltage	-0.5 to 30	V	



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Electrical Characteristics

 $T_A = 0$ - 70°C (unless otherwise specified). Typical values are measured at $T_A = 25^{\circ}$ C and $V_{CC} = 5V$

Emitter Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	IF = 16mA	-	1.45	1.6	V	
VR	Reverse Voltage	IR = 10μA	5.0	-	-	V	
ΔV _F /ΔT _A	Temperature coefficient of forward voltage	IF =16mA	-	-1.6	-	mV/°C	

Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Мах	Units	Notes
	Iон Logic High Output Current	I _F =0mA, V _O =V _{CC} =5.5V,	-	0.001	0.5	μА	
		T _A =25°C	,				
Іон		I _F =0mA, V _O =V _{CC} =15V,		0.01	1		
		T _A =25°C	-				
		I _F =0mA, V _O =V _{CC} =15V	-	-	50		
loo	Lania Laur Ouranto Ourana	I _F =16mA, V _O =Open,		120	200	μA	
ICCL	Logic Low Supply Current	Vcc=15V	-				
	Logic High Supply Current	I _F =0mA, V _O =Open, V _{CC} =15V,	-	0.01	1		
loou		T _A =25°C				۸	
Іссн		IF=0mA, VO=Open,			2	μΑ	
		VCC=15V	-	-			



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Transfer Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
	Current Transfer Ratio	I _F =16mA, V _O =0.4V,	20	-	50		
CTD		V _{CC} =4.5V, T _A =25°C	20			%	
CTR		I _F =16mA, V _O =0.5V,	15	-	-	70	
		V _{CC} =4.5V	15				
	Logic Low Output Voltage	I _F =16mA, I _O =3mA, V _{CC} =4.5V,	-	-	0.4		
		T _A =25°C				V	
Vol		I _F =16mA, I _O =2.4mA,	-	-	0.5	V	
		V _{CC} =4.5V					

Electrical Characteristics

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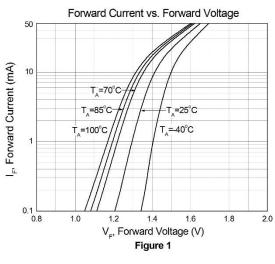
Switching Characteristics

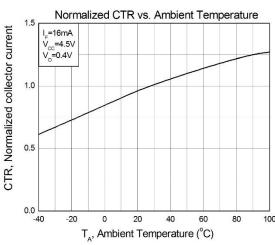
Symbol	Parameters		Test Conditions	Min	Тур	Max	Units	Notes
T_{PHL}	Propagation Delay Time Logic High to Logic Low		$I_F=16mA,\ R_L=1.9K\Omega,$ $T_A=25^{\circ}C$	-	0.35	0.8	μs	
			I _F =16mA, R _L =1.9K Ω	-	1	1.0		
T _{PLH}	Propagation Delay Time Logic Low		$I_F=16mA, R_L=1.9K\Omega,$ $T_A=25^{\circ}C$	-	0.3	0.8	μs	
	to Logic High $I_{\text{F}}\!=\!16\text{mA},R_{\text{L}}\!=\!1.9\text{K}\Omega \qquad \qquad -$	-	1	1.0				
CM	Common Mode	CTM452	$I_F = 0 mA$, $V_{CM}=10 Vp-p$, $R_L=1.9 K\Omega$, $T_A=25 ^{\circ} C$	5,000	-	-	V/	
СМн	Transient Immunity at Logic High	CTM453	$I_F = 0 mA \ , \ V_{CM} = 1500 Vp - p,$ $R_L = 1.9 K\Omega, \ T_A = 25 ^{\circ} C$	15,000	1		V/µs	
CML	Common Mode CTM452 Transient Immunity at Logic Low CTM453	CTM452	$I_F = 16 mA , V_{CM} = 10 Vp-p,$ $R_L = 1.9 K\Omega, T_A = 25 ^{\circ} C$	5,000	ı	ı	V/µs	
OIVIL		$I_F = 16 mA , V_{CM} = 1500 Vp-p,$ $R_L = 1.9 K\Omega, T_A = 25 ^{\circ}C$	15,000	-		ν/μ5		

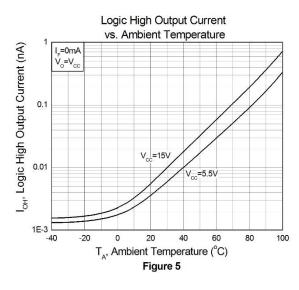


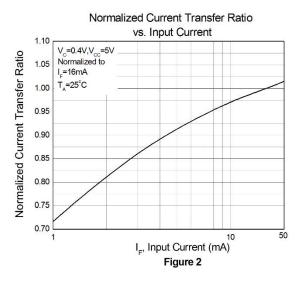
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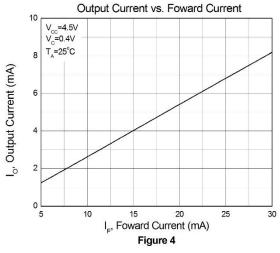
Typical Characteristic Curves

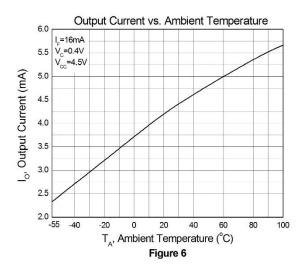








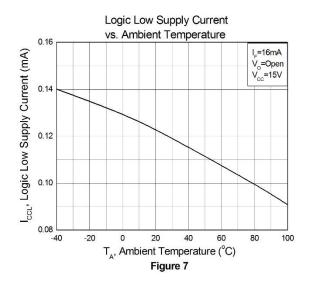


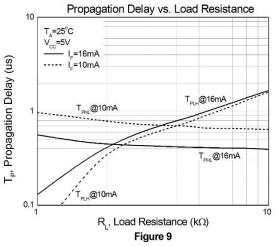


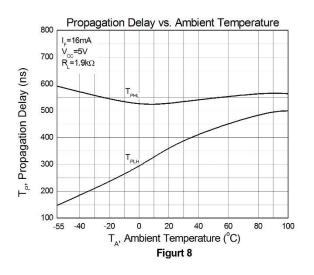


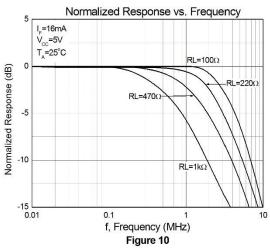
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Typical Characteristic Curves



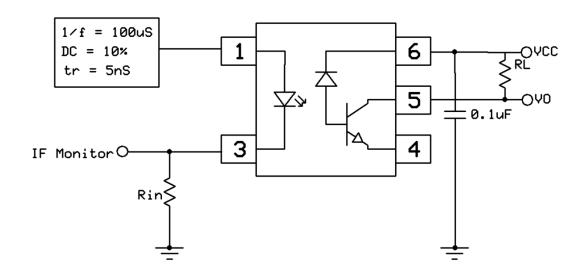


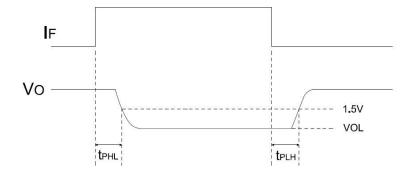




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Test Circuits



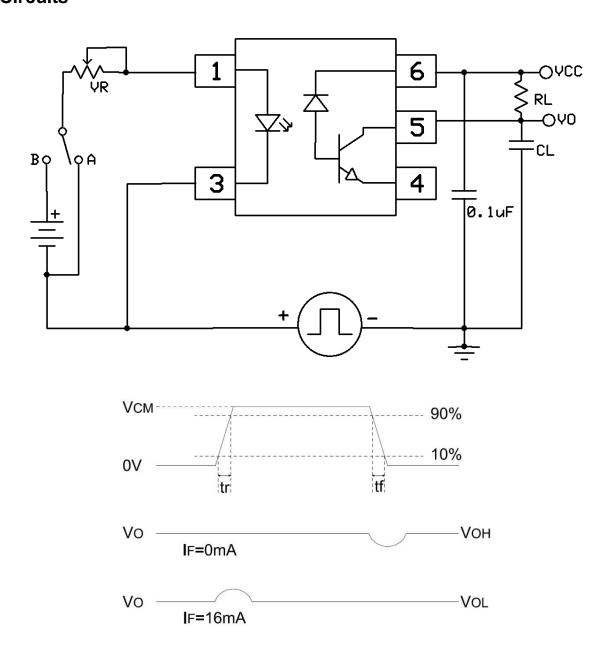


Switching Time Test Circuit



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Test Circuits

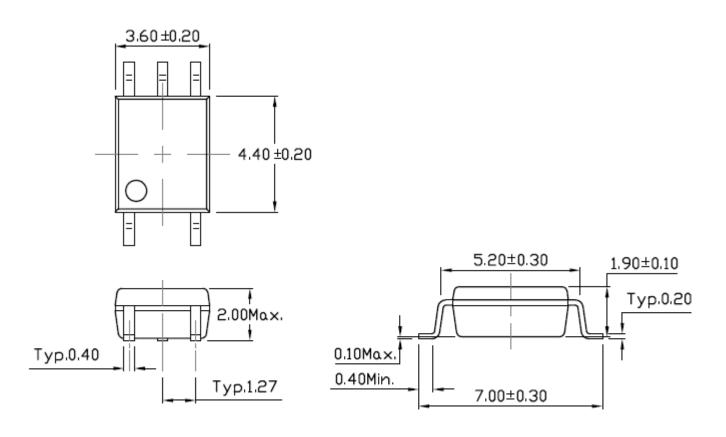


CMR Test Circuit

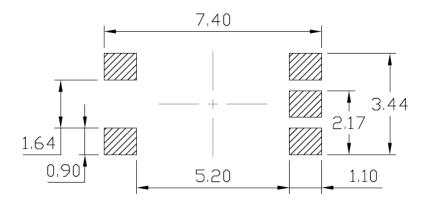


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Package Dimension Dimensions in mm unless otherwise stated



Recommended Solder Mask Dimensions in mm unless otherwise stated





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Marking Information



Note:

CT : Denotes "CT Micro"

M453 : Product Number

V : VDE Option
Y : Fiscal Year
WW : Work Week

K : Production Code

Ordering Information

CTM45X(V)(Z)

X = Part No. (X=2 or 3)

V = VDE Option (V or none)

Z = Tape and reel option (T1, T2, T3 or T4)

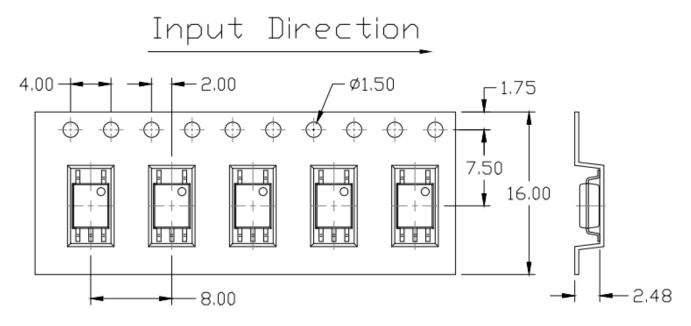
Option	Description	Quantity
T1	Surface Mount Lead Forming – With Option 1 Tapping	3000 Units/Reel
T2	Surface Mount Lead Forming – With Option 2 Tapping	3000 Units/Reel
Т3	Surface Mount Lead Forming – With Option 3 Tapping	3000 Units/Reel
T4	Surface Mount Lead Forming – With Option 4 Tapping	3000 Units/Reel



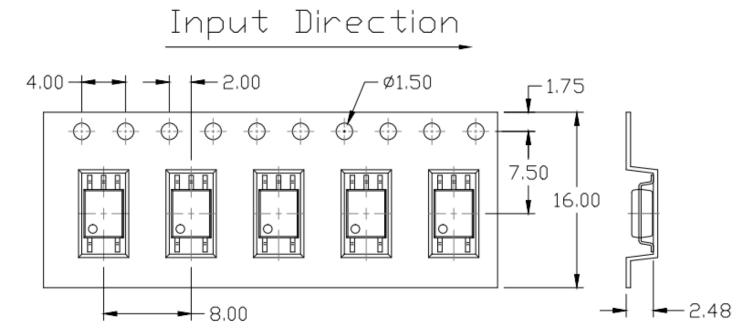
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Carrier Tape Specifications Dimensions in mm unless otherwise stated

Option T1



Option T2





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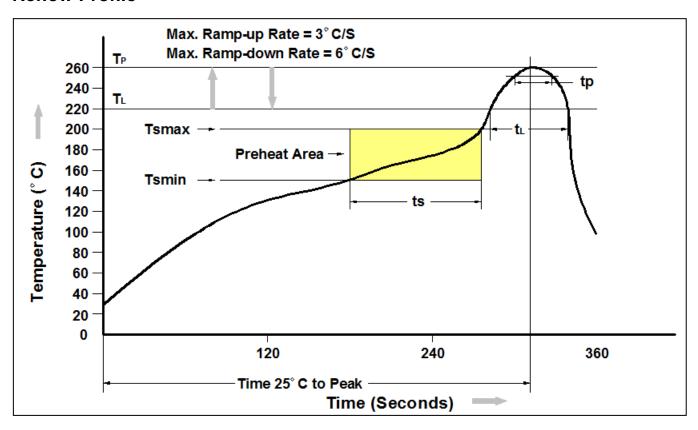
Option T3

Option T4



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Reflow Profile



Profile Feature	Pb-Free Assembly Profile			
Temperature Min. (Tsmin)	150°C			
Temperature Max. (Tsmax)	200°C			
Time (ts) from (Tsmin to Tsmax)	60-120 seconds			
Ramp-up Rate (t∟ to t _P)	3°C/second max.			
Liquidous Temperature (T _L)	217°C			
Time (t _L) Maintained Above (T _L)	60 – 150 seconds			
Peak Body Package Temperature	260°C +0°C / -5°C			
Time (t _P) within 5°C of 260°C	30 seconds			
Ramp-down Rate (T _P to T _L)	6°C/second max			
Time 25°C to Peak Temperature	8 minutes max.			



5 Pin Mini-Flat

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